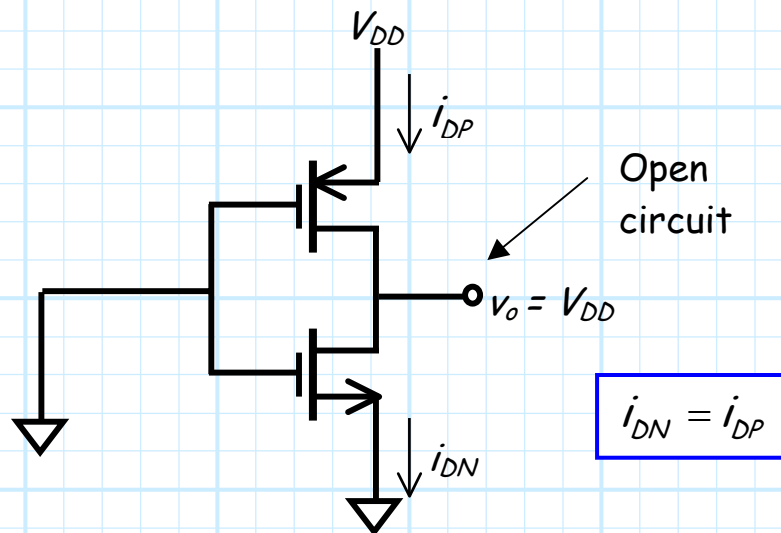
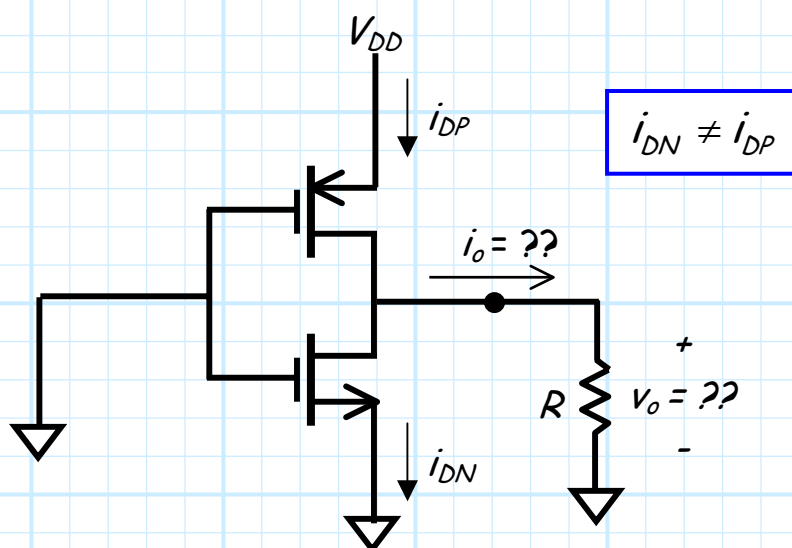


# The CMOS Model

Note that **all** our analysis of a CMOS inverter has been for the case where the output is connected to an **open circuit**, for example:



**Q:** What happens if we **connect** the CMOS inverter output to something?

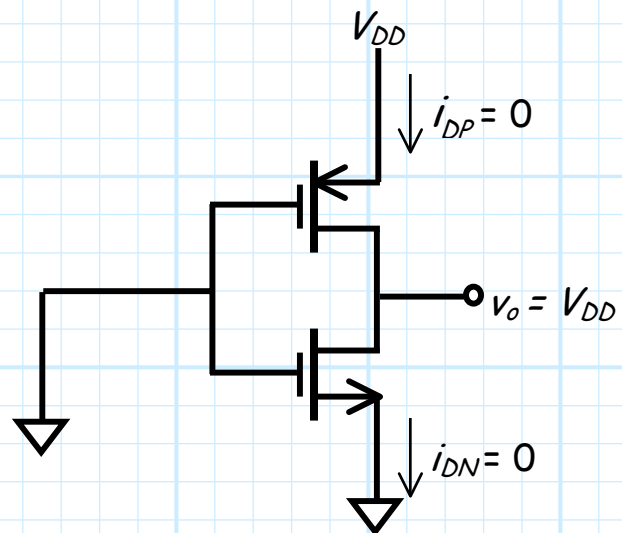


**A:** Note that now we have a **very** different circuit (e.g.,  $i_{DP} \neq i_{DN}$ ). We must use **CMOS model** to analyze the circuit!

Let's **again** look at the case with an **open** circuit at the output:

In this case,  $Q_P$  is in **Triode** and  $Q_N$  is in **Cutoff**.

In other words, the channel in the NMOS device is **not** conducting, but the channel in the PMOS device **is** conducting.



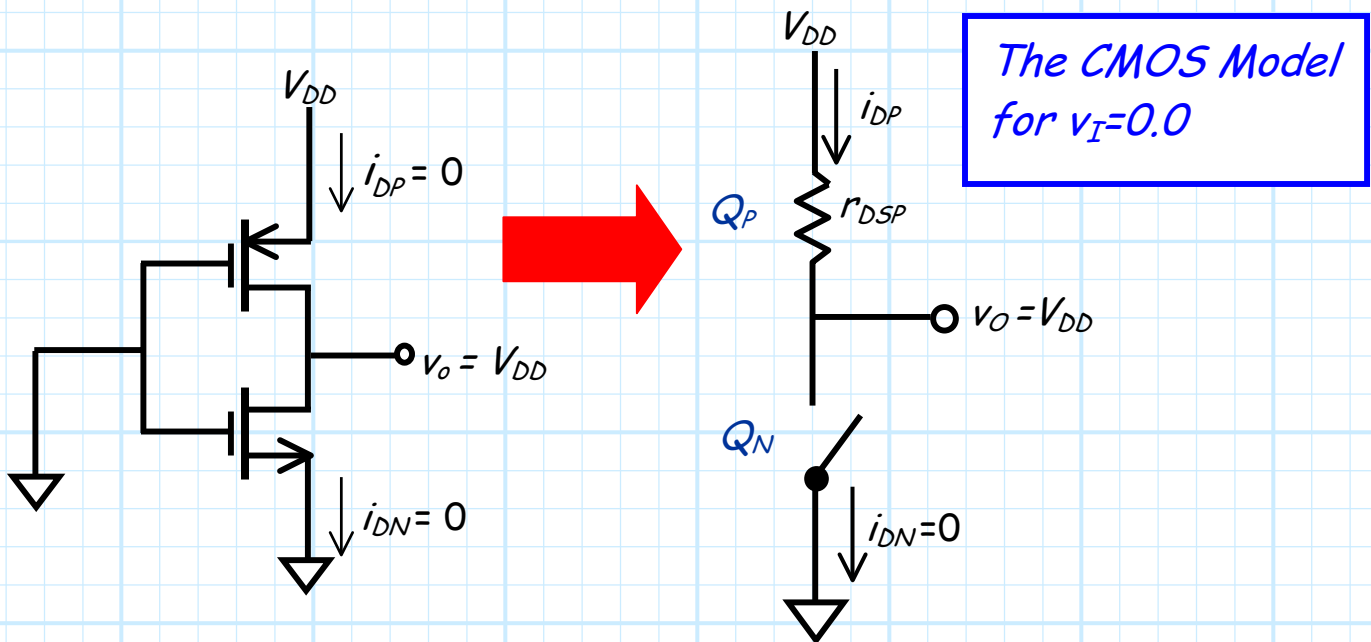
Moreover, since  $v_{DSP}$  is small (i.e.,  $v_{DSO} = v_o - V_{DD} = 0 \leftarrow$  **really** small!!), we can use the channel resistance approximation:

$$\frac{-v_{DSP}}{i_{DP}} \approx r_{DSP} = \frac{-1}{2K(v_{GSP} - V_{tp})}$$

In other words, the channel in the PMOS device acts like a **resistor** with resistance  $r_{DSP}$ ! Since  $v_{GSP} = -V_{DD}$ , we find:

$$\begin{aligned} r_{DSP} &= \frac{-1}{2K(-V_{DD} - V_{tp})} \\ &= \frac{1}{2K(V_{DD} + V_{tp})} \\ &= \frac{1}{2K(V_{DD} - V_t)} \end{aligned}$$

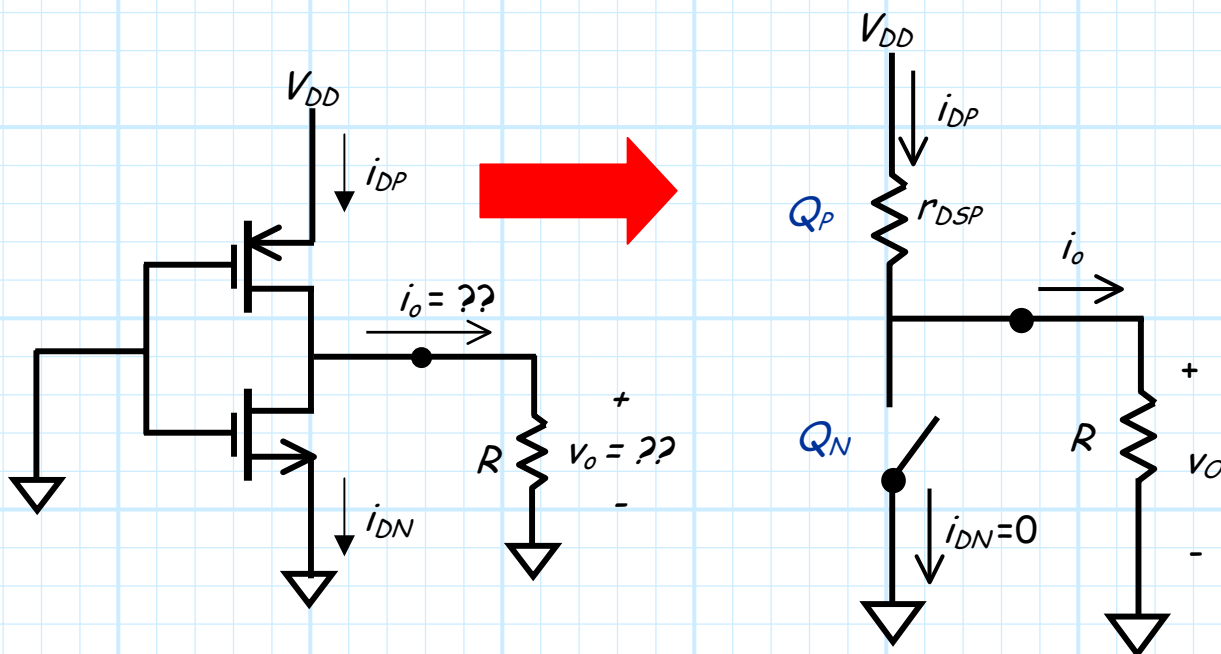
We can thus **model** the CMOS inverter as:



Note for **open** output circuit, we get the correct answer from this **model**:

$$i_D = 0 \quad \text{and} \quad v_O = V_{DD}$$

Now, let's see what happens if the output is **not open circuited**—let's place a load **resistor** at the output!:

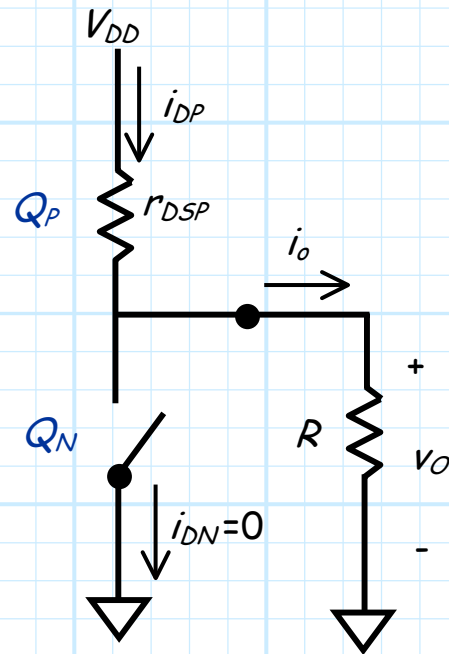


From the **model circuit**, we see that:

$$i_D = i_{DP} = \frac{V_{DD} - 0}{r_{DSP} + R} = \frac{V_{DD}}{r_{DSP} + R}$$

$$i_{DN} = 0$$

$$v_O = i_O R = V_{DD} \left( \frac{R}{r_{DSP} + R} \right)$$



Note, if  $R \gg r_{DSP}$ , then  $v_O$  will be **slightly** less than  $V_{DD}$ !

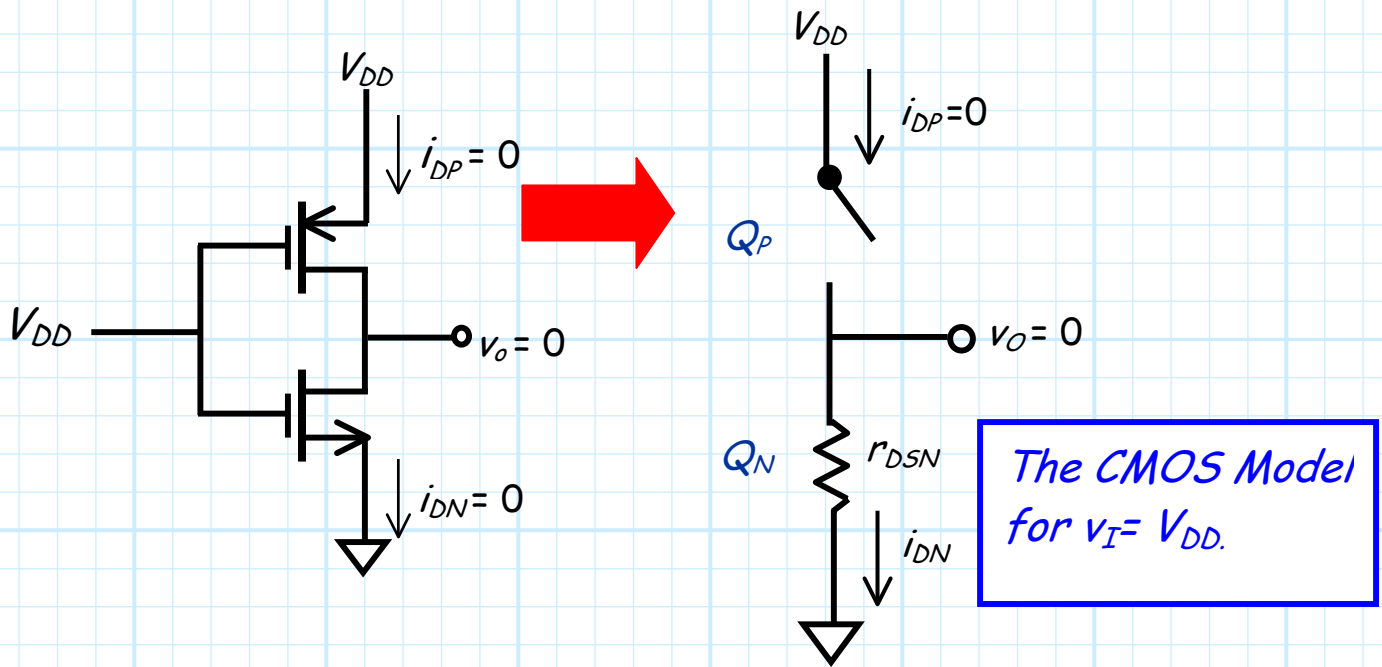
Note these are **approximate** values of  $i_{DP}$  and  $v_O$ , but if we solved the CMOS circuit directly (with **no** approximations), we would get answers **very** close to these.

In other words, the **CMOS model** is an accurate approximation provided that  $v_{DSP}$  is **small** enough.

**Q:** What happens if the input voltage to the CMOS inverter is high (i.e.,  $v_I = V_{DD}$ ) ??

In that case, **PMOS** device is in **cutoff** and the **NMOS** device is in **triode**.

Therefore the **CMOS model** for this condition is:



$$r_{DSN} = \frac{1}{2K(v_{GSN} - V_{tn})}$$

$$= \frac{1}{2K(V_{DD} - V_t)}$$

Note that  $r_{DSN} = r_{DSP}$  in for the **two** CMOS models!